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NTE4041 Integrated Circuit CMOS, Quad True/Complement Buffer 14-Lead DIP Type Package

Description:

The NTE4041 is a quad true/complement buffer in a 14-Lead DIP type package consisting of N-Channel and P-Channel units having low channel resistance and high current (sourcing and sinking) capability. This device is intended for use as a buffer, line driver, or CMOS-to-TTL driver. It can be used as an ultra-low power resistor-network driver for A/D and D/A conversion, as a transmission-line-driver, and in other applications where high noise immunity and low power dissipation are primary design requirements.

Features:

- Balanced Sink and Source Current: Approximately 4 Times Standard “B” Drive
- Equalized Delay to True and Complementary Outputs
- Maximum Input Current of 1μA at 18V over Full Package Temperature Range: 100nA at 18V and +25°C
- 5V, 10V, and 15V Parametric Ratings

Applications:

- High Current Source/Sink Driver
- CMOS-to-DTL/TTL Converter Buffer
- Display Driver
- MOS Clock Driver
- Resistor Network Driver (Ladder or Weighted R)
- Buffer
- Transmission Line Driver

Absolute Maximum Ratings:

DC Supply Voltage Range (Voltages referenced to V_{SS}), V_{DD}	-0.5 to +20.0V
Input Voltage Range (All Inputs)	-0.5 to $V_{DD} + 0.5V$
DC Input Current (Any One Input)	±10mA
Power Dissipation (Per Package), P_D	
For $T_A = -55^\circ$ to $+100^\circ C$	500mW
For $T_A = +100^\circ$ to $+125^\circ C$	Derate Linearity at 12mW/°C to 200mW
Device Dissipation (Per Output Transistor)	
For $T_A =$ Full Package Temperature Range	100mW
Operating Temperature Range, T_A	-55° to +125°C
Storage Temperature Range, T_{stg}	-65° to +150°C
Lead Temperature (During Soldering, 10sec max), T_L	+265°C

Recommended Operating Conditions:

DC Supply Voltage (For T_A = Full Package Temperature Range) 3 to 18V

Static Electrical Characteristics:

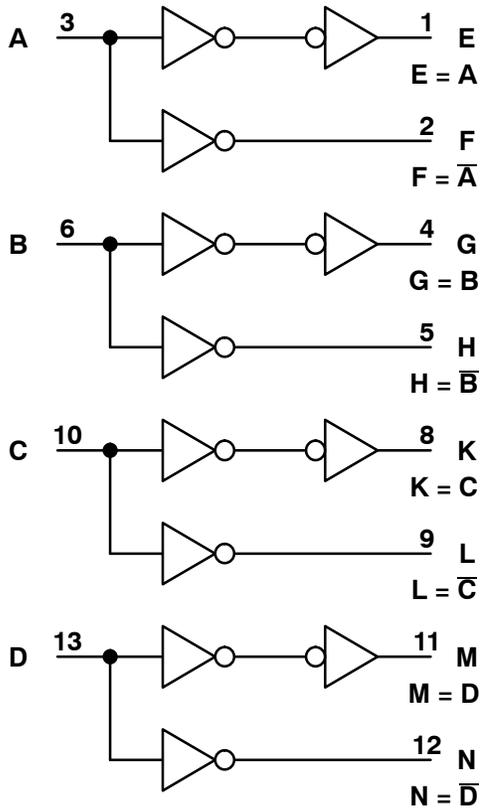
Characteristic	Conditions			Limits at Indicated Temperature (°C)							Units
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55°C	-40°C	+85°C	+125°C	+25°C			
								Min.	Typ.	Max.	
Quiescent Device Current I _{DD} Max	-	0,5	5	1.0	1.0	30	30	-	0.02	1.0	µA
	-	0,10	10	2.0	2.0	60	60	-	0.02	2.0	µA
	-	0,15	15	4.0	4.0	120	120	-	0.02	4.0	µA
	-	0,20	20	20	20	600	600	-	0.04	20	µA
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	2.1	1.8	1.3	1.2	1.6	3.2	-	mA
	0.5	0,10	10	6.25	5.6	4.0	3.5	5.0	10.0	-	mA
	1.5	0,15	15	24	23	15.5	13	19	38	-	mA
Output High (Source) Current I _{OH} Min.	4.6	0,5	5	-2.1	-1.8	-1.3	-1.2	-1.6	-3.2	-	mA
	2.5	0,5	5	-8.4	-6.7	-5.3	-4.6	-6.4	-12.8	-	mA
	9.5	0,10	10	-6.25	-5.6	-4.0	-3.5	-5.0	-10.0	-	mA
	13.5	0,15	15	-24	-23	-15.5	-13	-19	-38	-	mA
Output Voltage Low-Level V _{OL} Max.	-	5	5	0.05				-	0	0.05	V
	-	10	10	0.05				-	0	0.05	V
	-	15	15	0.05				-	0	0.05	V
Output Voltage High-Level V _{OH} Min.	-	5	5	4.95				4.95	5	-	V
	-	10	10	9.95				9.95	10	-	V
	-	15	15	14.95				14.95	15	-	V
Input Low Voltage V _{IL} Max.	0,5,4,5	-	5	1.0				-	-	1.0	V
	1,9	-	10	2.0				-	-	2.0	V
	1,5,13,5	-	15	2.5				-	-	2.5	V
Input High Voltage V _{IH} Min.	0,5,4,5	-	5	4.0				4.0	-	-	V
	1,9	-	10	8.0				8.0	-	-	V
	1,5,13,5	-	15	12.5				12.5	-	-	V
Input Current, I _{IN} Max.	-	0,18	18	±0.1	±0.1	±1.0	±1.0	-	±10 ⁻⁵	±0.1	µA

Dynamic Electrical Characteristics:

(T_A = +25°C, C_L = 50pF, R_L = 200kΩ, t_r and t_f = 20ns unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Propagation Delay Time from	t _{PHL} or t _{PLH}	V _{DD} = 5V	-	60	120	ns
		V _{DD} = 10V	-	35	70	ns
		V _{DD} = 15V	-	25	50	ns
Transition Time	t _{THL} or t _{TLH}	V _{DD} = 5V	-	40	80	ns
		V _{DD} = 10V	-	20	40	ns
		V _{DD} = 15V	-	15	30	ns
Input Capacitance	C _{IN}	Any Input	-	15.0	22.5	pF

Logic Diagram



$V_{DD} = \text{Pin14}$
 $V_{SS} = \text{Pin7}$

Pin Connection Diagram

